T1M80120J

SiC N-MOSFET 1200V, 75mΩ, 30A

Features

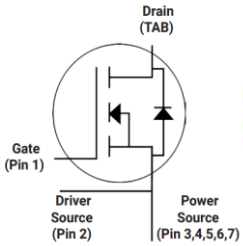
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Avalanche Ruggednes

Product Summary

V_{DS}	1200V
$R_{DS(on)\_typ}$	75mΩ
I_D	30A

Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC-DC Converte
- Batterry Chargers



RoHS

Halogen Free

Package Marking and Ordering Information

Part #	Marking	Package
T1M80120J	1M80120J	TO-263-7

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	1200	V
Continuous drain current T_C = 25°C ,Vgs=18V T_C = 100°C ,Vgs=18V	I_D	 30 21	A
Source current(Body Diode) T_C = 25°C ,Vgs=-4V T_C = 100°C ,Vgs=-4V	I_S	 30 21	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	80	A
Avalanche energy, single pulse (L=10mH)	E_{AS}	600	mJ
Gate-Source voltage	V_{GS}	-4/+18	V
Gate-Source voltage（Absolute maximum values）	V_{GSmax}	-8/+22	V
Power dissipation (T_C = 25°C)	P_{tot}	136	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+175	°C

•Example of acceptable V_{GS} waveform

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Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	1.1	°C/W
Thermal resistance, junction – ambient. Max	R_{thJA}	40	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	V_{DSS}	1200	-	-	V	V_{GS}=0V, I_D=100uA
Gate threshold voltage	$V_{GS(th)}$	2.3	2.8	3.6	V	V_{DS}=V_{GS},I_D=5mA
Zero gate voltage drain current	I_{DSS}	-	1	10	μA	V_{DS}=1200V,V_{GS}=0V T_C=25°C
		-	5	-		T_C=175°C
Gate-source leakage current	I_{GSS}	-		100	nA	V_{GS}=18V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	75	85	mΩ	V_{GS}=18V, I_D=20A, T_J=25°C
		-	125	-		T_J=175°C
Transconductance	g_{fs}	-	10	-	S	V_{DS}=20V,I_D=20A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	920	-	pF	V_{DS} = 1000V V_{GS} = 0V T_J = 25°C V_{AC} = 25mV f = 1MHz
Output Capacitance	C_{oss}	-	57	-		
Reverse Transfer Capacitance	C_{rss}	-	3.9	-		
Gate Total Charge	Q_G	-	40	-	nC	V_{DS} = 800V V_{GS} = -4/18V I_D = 20A
Gate-Source charge	Q_{gs}	-	7	-		
Gate-Drain charge	Q_{gd}	-	19	-		
Turn-On Switching Energy	E_{ON}	-	320	-	μJ	V_{DD} = 800V V_{GS} = -4/+15V I_D = 20A R_G = 0Ω L = 120uH
Turn-Off Switching Energy	E_{OFF}	-	49	-		
Turn-on delay time	$t_{d(on)}$	-	19	-	ns	
Rise time	t_r	-	21	-		
Turn-off delay time	$t_{d(off)}$	-	15	-		
Fall time	t_f	-	17	-		
Gate resistance	R_G	-	1.5	-	Ω	V_{AC} = 25mV, f=1MHz

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Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	4.2	-	V	V_{GS}=-4V,I_{SD}=10A, T_J=25°C
		-	3.8	-		V_{GS}=-4V,I_{SD}=10A, T_J=175°C
Body Diode Forward Current	I_{SD}	-	-	30	A	V_{GS}=-4V,T_J=25°C
Pulsed Body Diode Forward Current	I_{SDM}	-	-	89		
Reverse Recovery Time	t_{rr}	-	39.6	-	ns	V_R = 800V, V_{GS} = -4V I_D = 20A di/dt = 700A/μS T_J = 25°C
Reverse Recovery Charge	Q_{rr}	-	141.1	-	nC	
Reverse Recovery Energy	E_{REC}	-	62.9	-	uJ	
Peak Reverse Recovery Current	I_{rrm}	-	6.2	-	A	
Charge Time	t_A	-	9.9	-	ns	
DisCharge Time	t_B	-	29.7	-	ns	
Reverse Recovery Time	t_{rr}	-	45.4	-	ns	V_R = 800V, V_{GS} = -4V I_D = 20A di/dt = 700A/μS T_J = 175°C
Reverse Recovery Charge	Q_{rr}	-	397	-	nC	
Reverse Recovery Energy	E_{REC}	-	180.1	-	uJ	
Peak Reverse Recovery Current	I_{rrm}	-	13.8	-	A	
Charge Time	t_A	-	30.8	-	ns	
DisCharge Time	t_B	-	14.9	-	ns	

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Typical Performance Characteristics

Fig 1. Output Characteristic (T_J=-40℃)

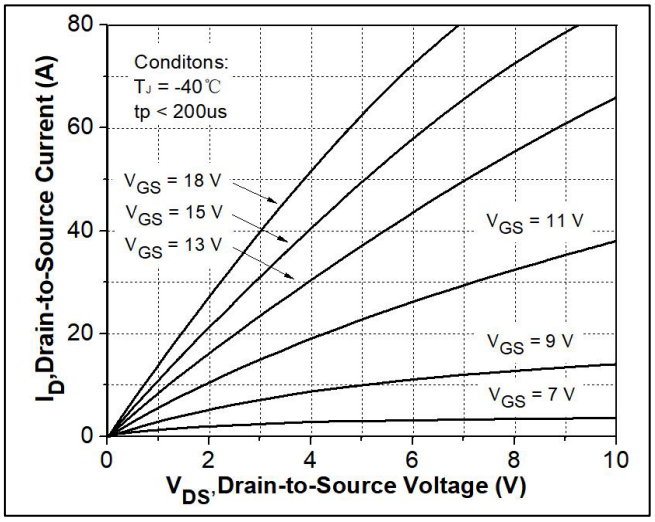

Fig 2. Output Characteristic (T_J=25℃)

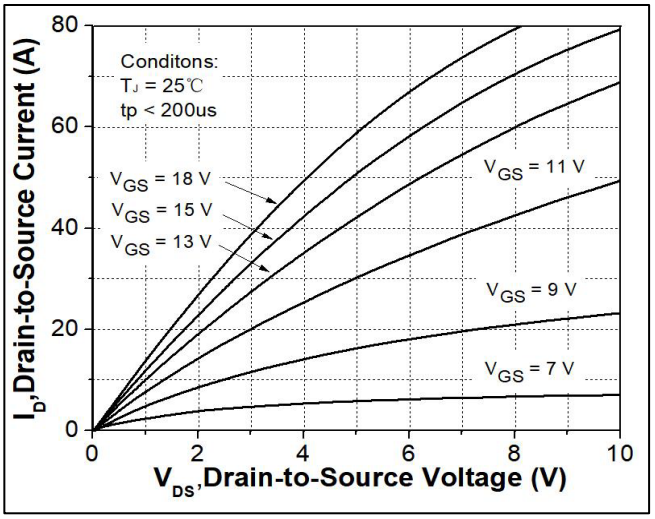

Fig 3. Output Characteristic (T_J=175℃)

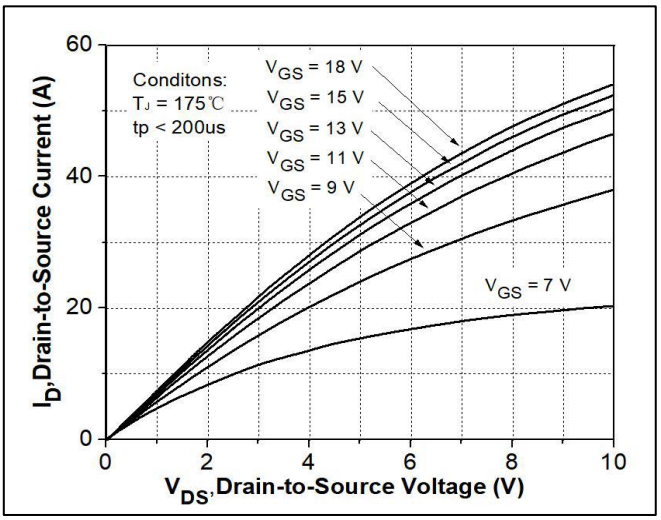

Fig 4: Rdson Vs Ids Characteristic

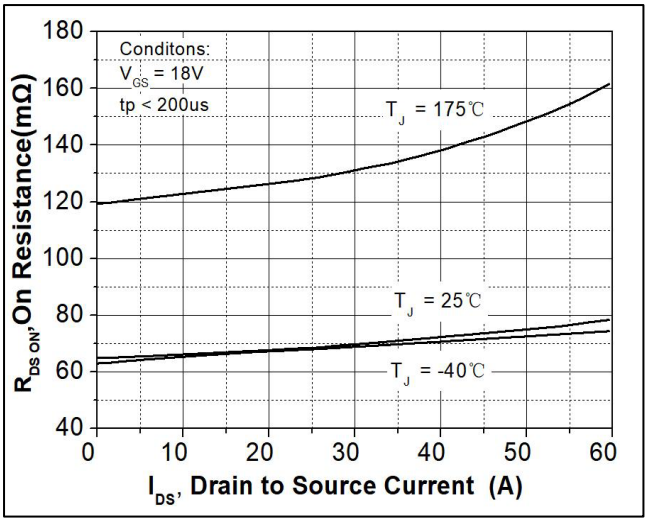

Fig 5: Rds(on) vs. Temperature

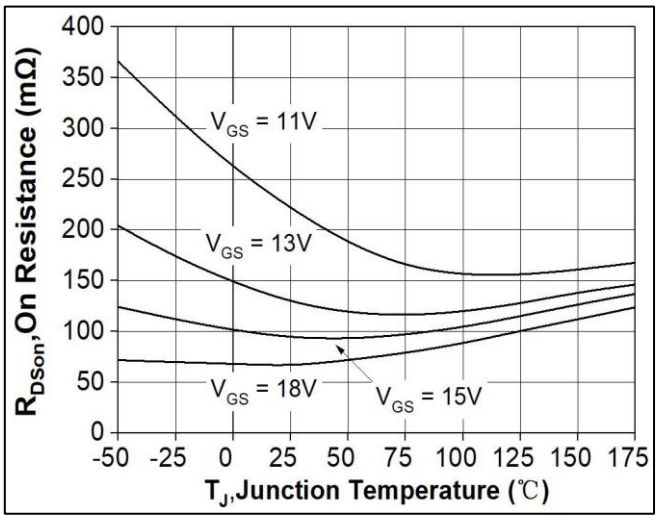

Fig 6: Transfer Characteristic

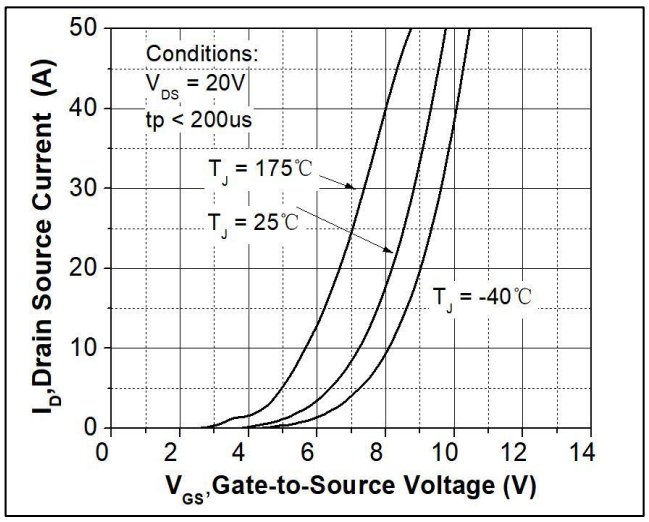

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Fig 7: Body-diode Characteristic (T_J=-40℃)

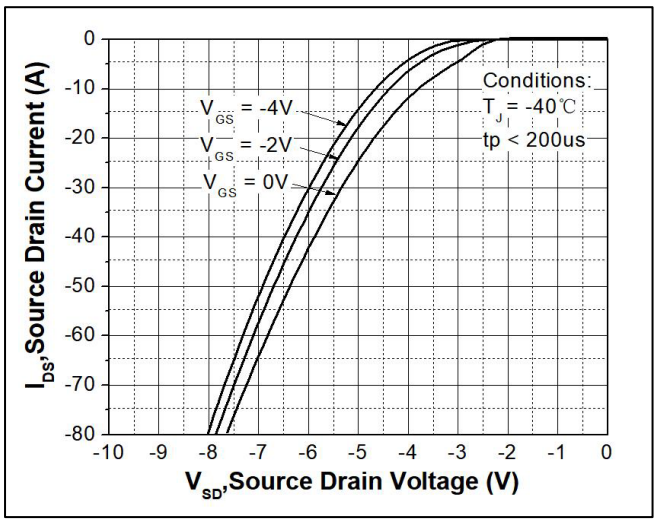

Fig 8: Body-diode Characteristic (T_J=25℃)

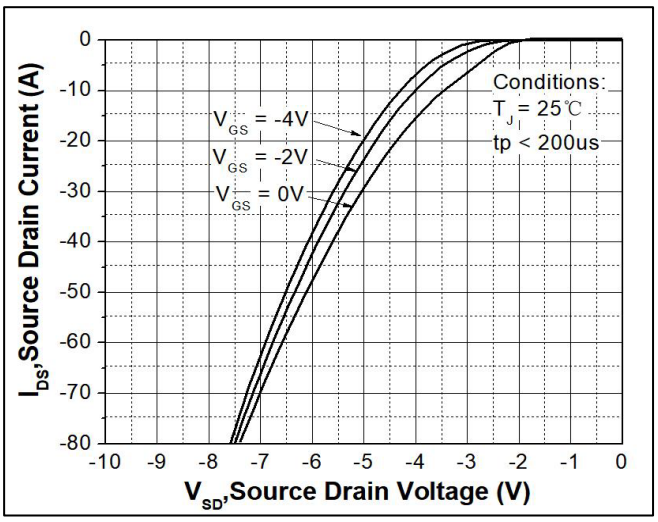

Fig 9: Body-diode Characteristic (T_J=175℃)

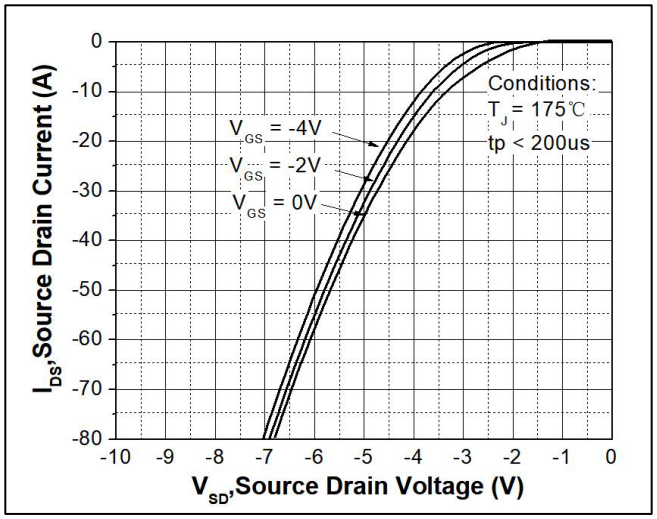

Fig 10: V_{TH} Vs T_J Temperature Characteristic

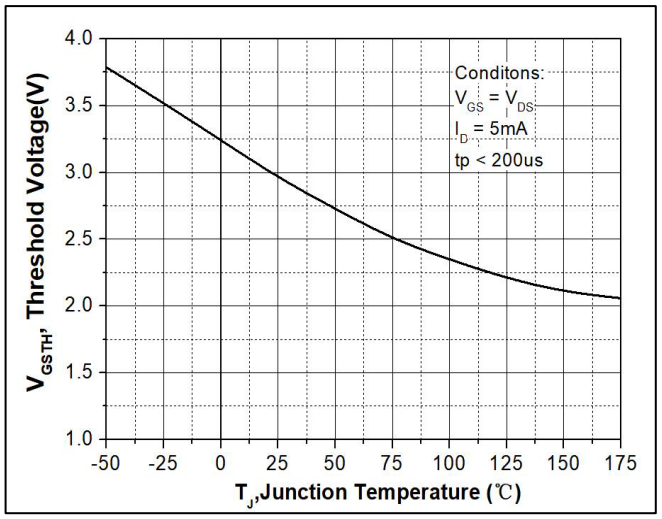

Fig 11: Gate Charge Characteristics

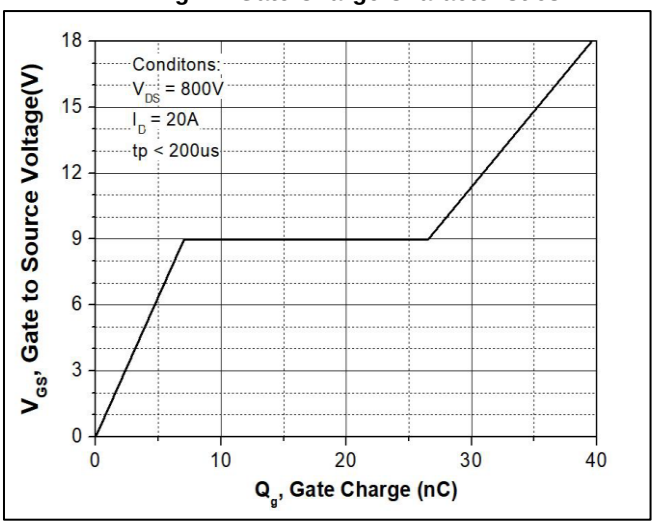

Fig 12: 3rd Quadrant Characteristic(T_J=-40°C)

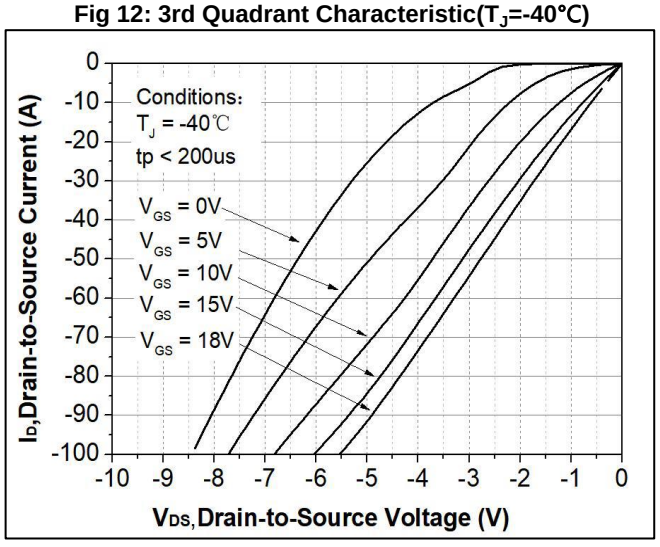

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Fig 13: 3rd Quadrant Characteristic(T_J=25℃)

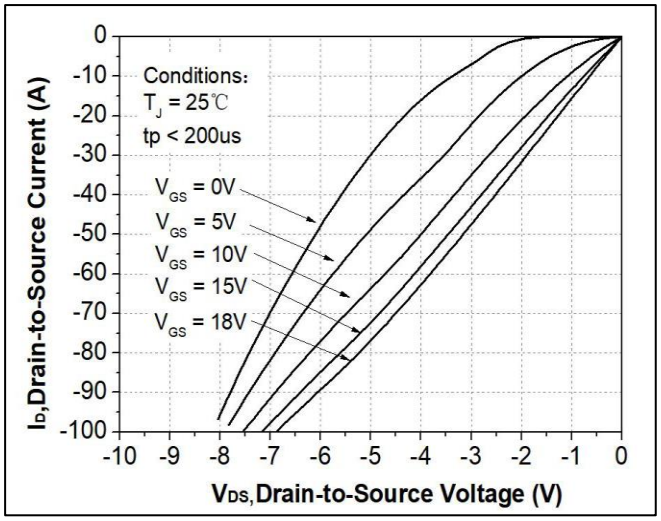


Fig 14: 3rd Quadrant Characteristic(T_J=175℃)

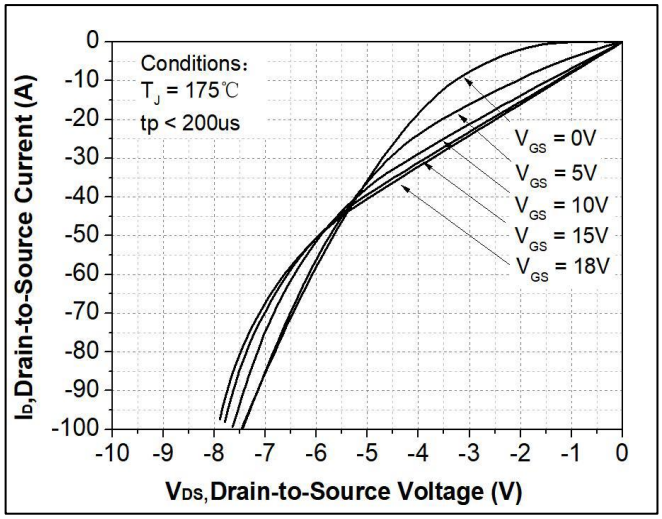


Fig 15: Capacitance Characteristic

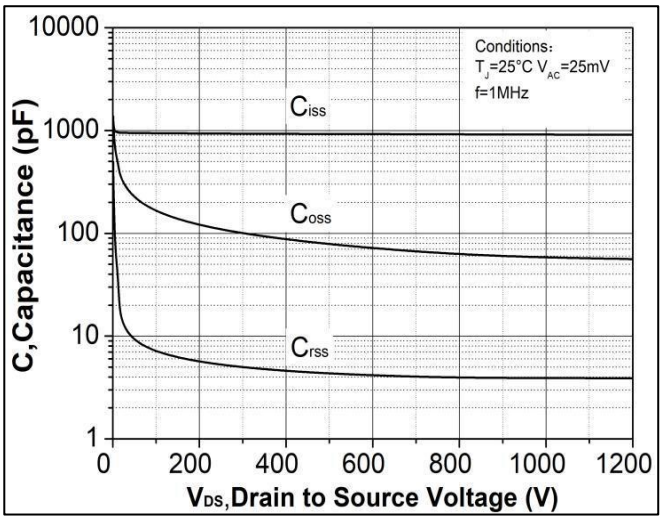


Fig 16: Safe Operating Area

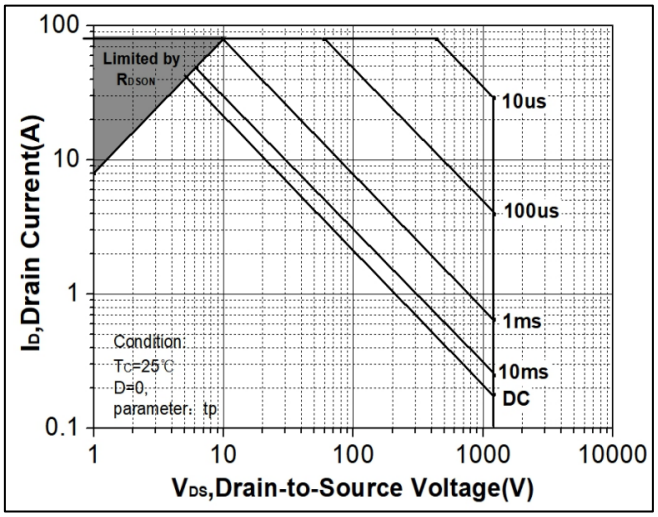
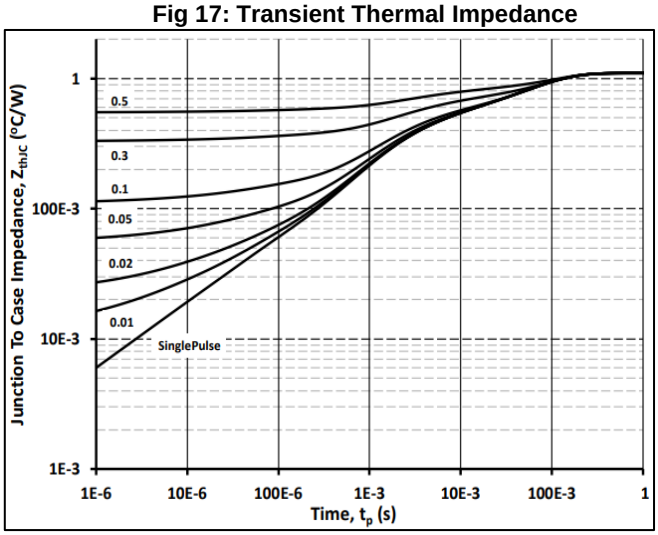


Fig 17: Transient Thermal Impedance



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Test Circuit & Waveform

Figure A. Definition of switching times

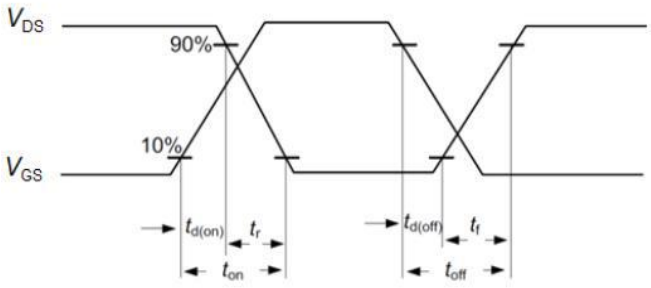

Figure B. Dynamic test circuit

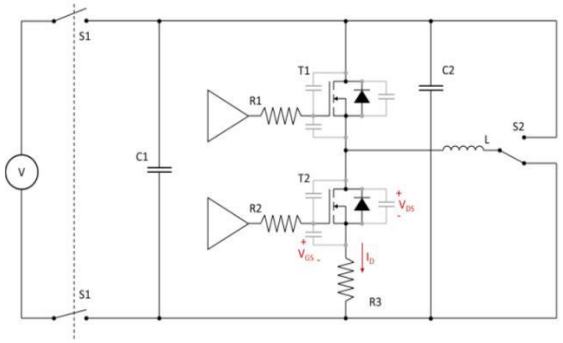

Figure C. Definition of body diodeswitching characteristics

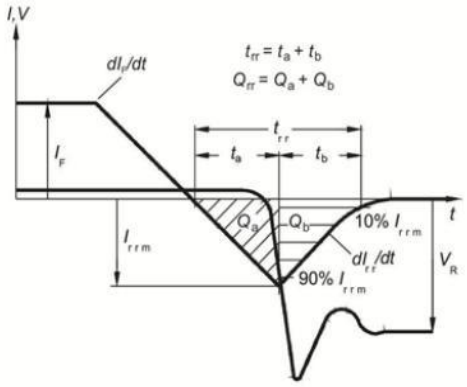

Figure C. **Definition of diode switching characteristics**

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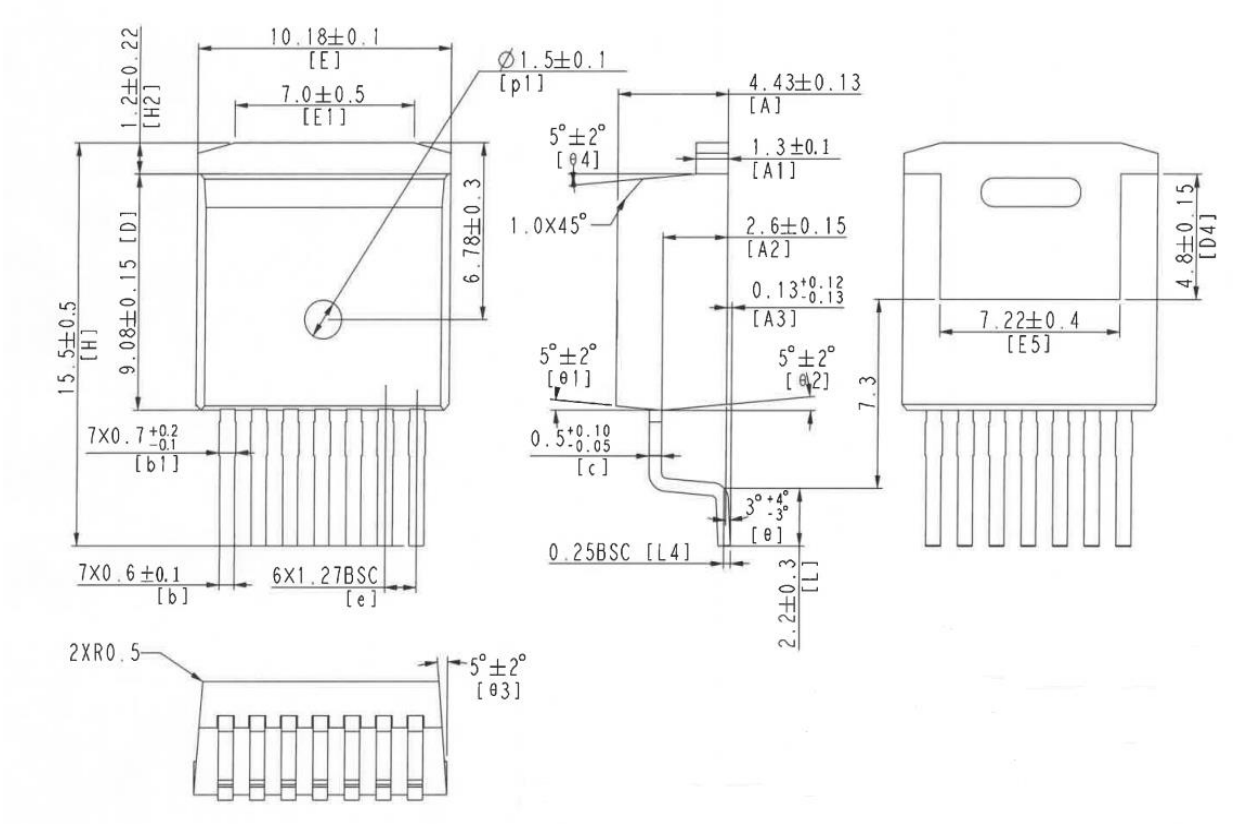
Package Outline:

UNIT:mm



Contact Information

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For additional information, please contact your local Sales Representative.

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